RoHS

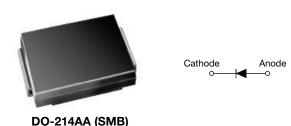
COMPLIANT HALOGEN

FREE



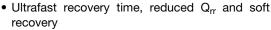
Vishay Semiconductors

Ultrafast Rectifier, 2 A FRED Pt®



PRODUCT SUMMARY				
Package	DO-214AA (SMB)			
I _{F(AV)}	2 A			
V _R	200 V			
V _F at I _F	0.66 V			
t _{rr} typ.	24 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES





- Specific for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, ultrafast recovery time, and fast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, output operation, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current	I _{F(AV)}	T _L = 150 °C ⁽¹⁾	2	V
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	70	Α
Operating junction and storage temperatures	T _J , T _{Sta}		-65 to +175	°C

Note

⁽¹⁾ Mounted on PCB with 6 mm x 3.5 mm lands

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-	.,	
Forward voltage	V_{F}	I _F = 2 A	-	0.84	0.9	V	
Forward voltage	VF	I _F = 2 A, T _J = 150 °C	-	0.66	0.7		
Develope legisles a summert		V _R = V _R rated	-	-	2		
Reverse leakage current	I _R	T _J = 150 °C, V _R = V _R rated	-	-	20	μA	
Junction capacitance	C _T	V _R = 200 V	-	12	-	pF	
Critical rate if rise of reverse voltage	dV/dt_{τ}		-	-	10 000	V/µs	



Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	24	-	ns
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A/}\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	27	-	
Reverse recovery time t _{rr}	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	23		
	T _J = 25 °C		-	21	-		
	T _J = 125 °C		-	26	-		
Pook rocovony ourront	Peak recovery current I _{RRM} -	T _J = 25 °C	l _F = 2 A dl _F /dt = 200 A/μs	-	2.7	-	Α
reak recovery current		T _J = 125 °C	$V_{R} = 100 \text{ V}$	-	3.4	-	^
Reverse recovery charge Q _{rr}	T _J = 25 °C		-	28	-	nC	
	T _J = 125 °C		-	43	-		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case	R _{thJC} ⁽¹⁾		-	-	17	°C/W
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾		-	-	80	C/VV
Approximate Weight				0.1		g
Approximate Weight			0.003		OZ.	
Marking device		Case style DO-214AA (SMB)		21	1 2	

Note

⁽¹⁾ Units mounted on PCB 6 mm x 3.5 mm land areas

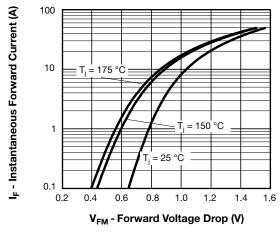


Fig. 1 - Typical Forward Voltage Drop Characteristics

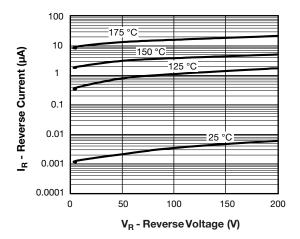


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

Vishay Semiconductors

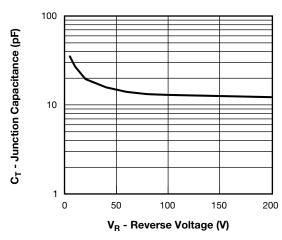


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

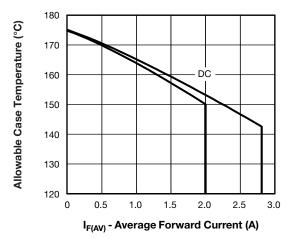


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

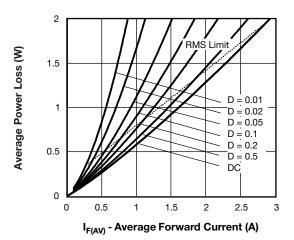


Fig. 5 - Forward Power Loss Characteristics

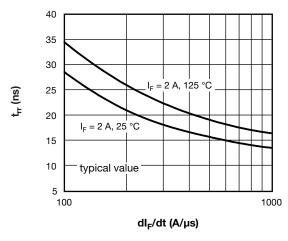


Fig. 6 - Typical Reverse Recovery vs. dl_F/dt

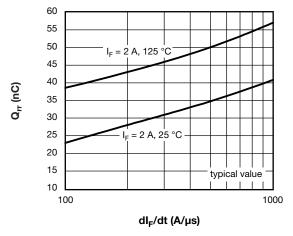
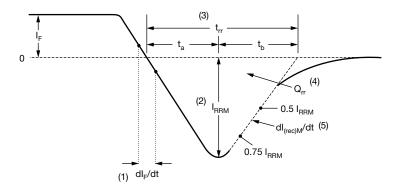


Fig. 7 - Typical Stored Charge vs. dl_F/dt

www.vishay.com

Vishay Semiconductors



- (1) dl_F/dt rate of change of current through zero crossing
 - ossing and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(4) Q_{rr} - area under curve defined by t_{rr}

- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (5) $dI_{(rec)M}/dt$ peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION (Example)				
PREFERRED P/N	PACKAGE CODE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-2EGH02HM3/5BT	5BT	3200	13"diameter plastic tape and reel	
VS-2EGH02HM3_A/I	I	3200	13"diameter plastic tape and reel	

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95401			
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			
SPICE model	www.vishay.com/doc?96021			

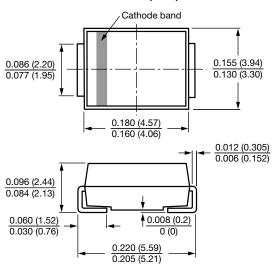


Vishay Semiconductors

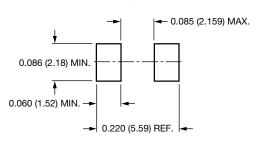
SMB

DIMENSIONS in inches (millimeters)

DO-214AA (SMB)



Mounting Pad Layout





Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.